RB521C30

Schottky Barrier Diode **http://www.willsemi.com**

Features

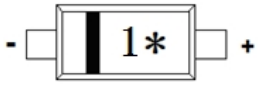
- 100mA Average rectified forward current
- Low forward voltage
- Low leakage current
- Small package SOD-923

SOD-923

Circuit

Applications

- Low Current rectification



Marking

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	30	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_O	100	mA
Peak forward surge current (8.3ms single sine pluse)	I_{FSM}	0.5	A
Junction temperature	T_J	150	°C
Operating temperature	Topr	-40 ~ 125	°C
Storage temperature	Tstg	-40 ~ 150	°C

Electronics characteristics (T_A=25°C)

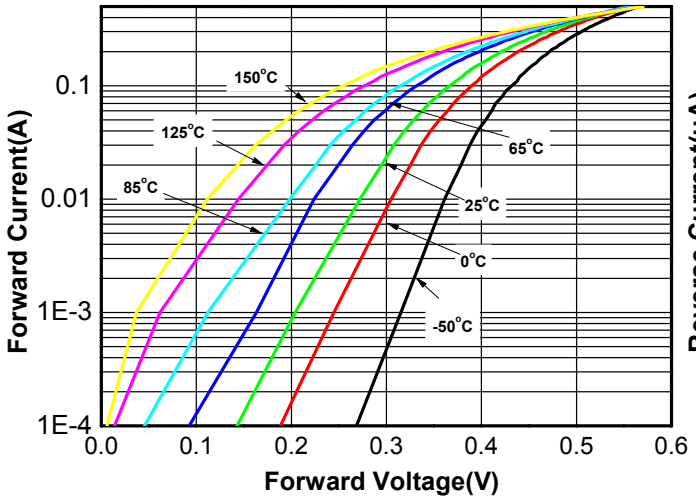
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Voltage	V_R	I_R=100uA	30			
Forward Voltage	V_F	I_F=10mA			0.35	V
		I_F=100mA			0.47	V
Reverse current	I_R	V_R=10V			6	uA
		V_R=30V			15	uA
Junction capacitance	C_J	V_R=5V, F=1MHz		21		pF
Thermal Resistance	$R_{\theta(JA)}$	Junction to Ambient		650		K/W

Order Informations

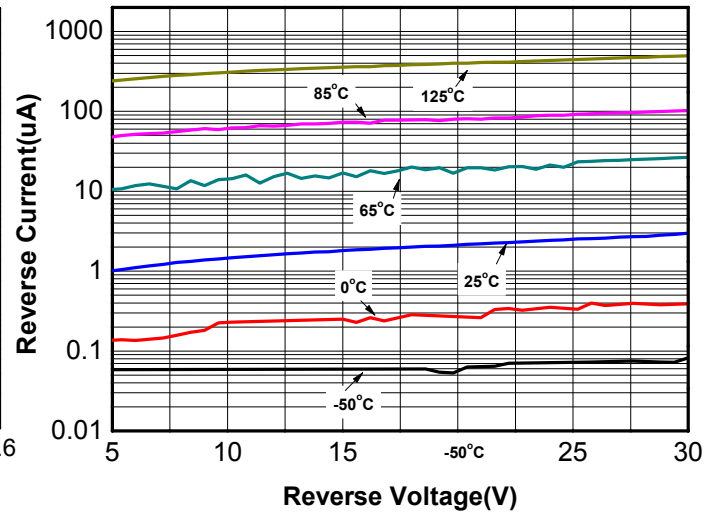
Device	Package	Marking	Shipping
RB521C30-2/TR	SOD-923	1* (1)	10000/Reel&Tape

Note 1：*= Month code(A~Z);1= Device code;

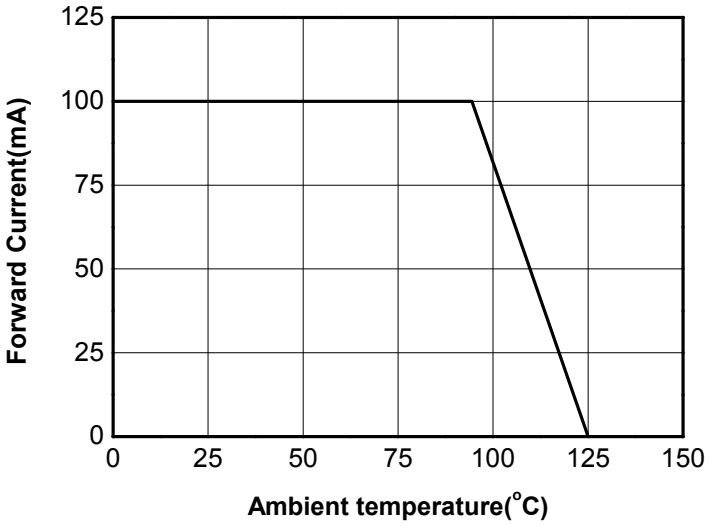
Typical characteristics (Ta=25°C, unless otherwise noted)



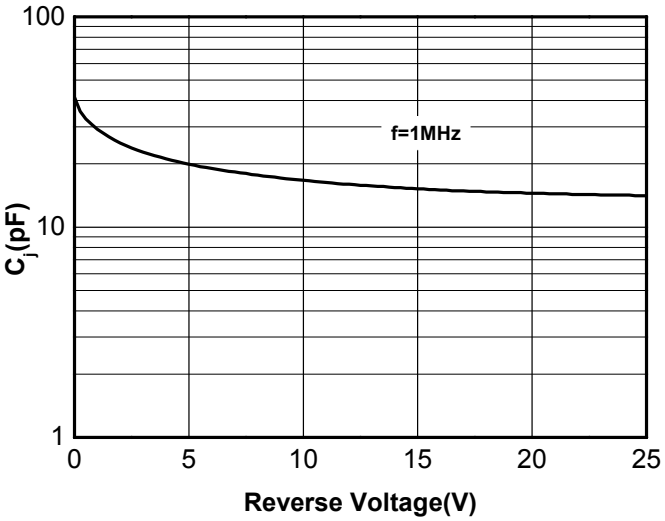
Forward voltage vs. Forward current



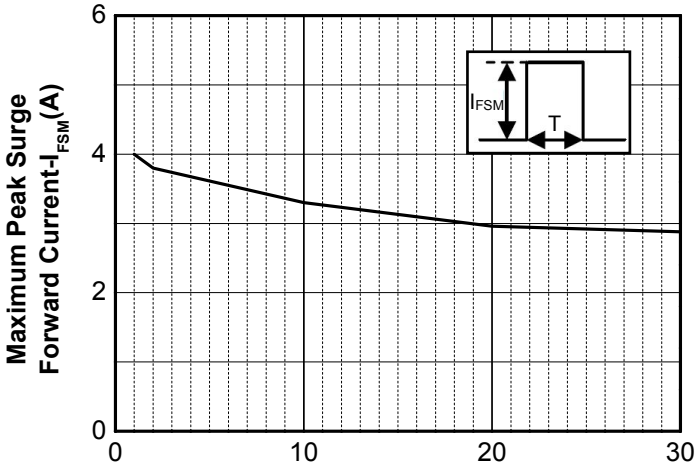
Reverse current vs. Reverse voltage



Forward current derating curve



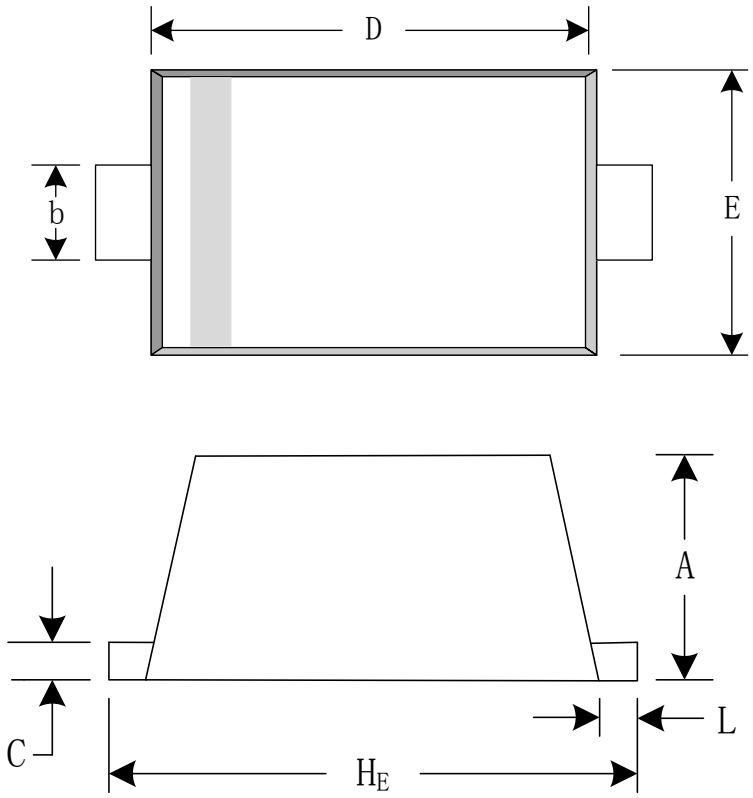
Junction capacitance vs. Reverse voltage



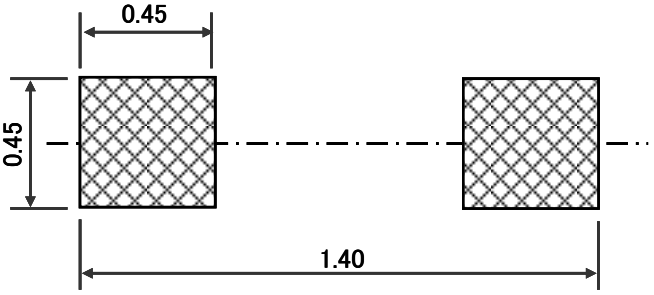
IFSM-T Characteristics

Package outline dimensions

SOD-923



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.36	0.40	0.45
b	0.15	0.20	0.30
C	0.05	0.12	0.20
D	0.70	0.80	0.90
E	0.55	0.60	0.65
H_E	0.90	1.00	1.10
L	0.05	0.10	0.15



Land Pattern Recommendation